



INFORMATION DISCLOSURE STATEMENT

Applicant : Tomasini et al.
App. No : 10/799,335
Filed : 12 March 2004
For : METHOD TO PLANARIZE AND
REDUCE DEFECT DENSITY OF
SILICON GERMANIUM
Examiner : Unknown
Art Unit : 2812

CERTIFICATE OF MAILING

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

27 September 2005

(Date)

Kyle F. Schlueter
Kyle F. Schlueter, Reg. No. 54,912

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application is a PTO/SB/08 Equivalent listing 21 references to be considered by the Examiner. Also enclosed are 13 foreign patent references and/or non-patent literature as listed on the Information Disclosure Statement.

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required. If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 27 sep 05

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

	Application No.	10/799,335
	Filing Date	12 March 2004
	First Named Inventor	Pierre Tomasini
	Art Unit	2812
(Multiple sheets used when necessary)	Examiner	Unknown
SHEET 1 OF 2	Attorney Docket No.	ASMEX.447A

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
	1	6,875,279	04/2005	Chu et al.	
	2	2003/0445063	03/2003	Hernandez et al.	
	3	2003/0082300	05/2003	Todd et al.	
	4	2003/0124818	07/2003	Luo et al.	
	5	2003/0157787	08/2003	Murthy et al.	
	6	2003/0207127	11/2003	Murthy et al.	
	7	2003/0235931	12/2003	Wada et al.	
	8	2005/0079692	04/2005	Samoilov et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹
	9	EP 0858101	02/1998	Aoyama, Tohru		
	10	WO 00/15885	03/2000	Hernandez et al.		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
	11	CANNON, D. et al., "Tensile strained epitaxial Ge films on Si(100) substrates with potential application in L-band telecommunications," Applied Physics Letter, Volume 84, Number 6, February 9, 2004, pp. 906-908	
	12	COLACE, L. et al., "Efficient high-speed near-infrared Ge photodetectors integrated on Si substrates," Applied Physics Letters, Volume 76, Number 10, March 6, 2000, pp. 1231-1233	
	13	COLACE, L. et al., "Ge-on-Si Approaches to the Detection of Near-Infrared Light," IEEE Journal of Quantum Electronics, Vol. 35, No. 12, December 1999, pp. 1843-1852	
	14	FAMA, S. et al., "High performance germanium-on silicon detectors for optical communications," Applied Physics Letters, Volume 81, Number 4, July 22, 2002, pp. 586-588	
	15	HULL, R., "Metastable strained layer configurations in the SiGe/Si System," (1999) EMIS Datareviews, Series No. 24 of SiGe and SiGe:C, edited by Erich Kasper et al., INSPEC (2000), London, UK	
	16	ISHIKAWA, Y. et al., "Strain-induced band gap shrinkage in Ge grown on Si substrate," Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046	
	17	LEE et al., "Growth of strained Si and strained Ge heterostructures on relaxed Si _{1-x} Ga _x Gaby ultrahigh vacuum chemical vapor deposition," J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004).	

Examiner Signature	Date Considered
<p>*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

T¹ - Place a check mark in this area when an English language Translation is attached.

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	18	LI, Q, et al., "Selective growth of Ge on Si(100) through vias of SiO ₂ nanotemplate using solid source molecular beam epitaxy," Applied Physics Letters, Volume 83, Number 24, December 15, 2003, pp. 5032-5034	
	19	LIU, J. et al., "Silicidation -induced band gap shrinkage In Ge epitaxial films on Si," Applied Physics Letters, Volume 84, Number 5, February 2, 2004, pp. 660-662	
	20	MASINI, G. et al., "High-Performance p-i-n Ge on Si Photodetectors for the Near Infrared: From Model to Demonstration," IEEE Transactions of Electron Devices, Vol. 48, No. 6, June 2001, pp. 1092-1096	
	21	SCHOLLHORN et al., "Coalescence of germanium islands on silicon," Thin Solid Films, " Vol. 336 (1988), pp. 109-111	

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